

Features

- For surface mount applications
- Glass Passivated Chip Junction
- Low profile package

SMA



1.Cathode —|<— 2.Anode

Marking Code:

M1G-PJ: M1
M2G-PJ: M2
M3G-PJ: M3
M4G-PJ: M4
M5G-PJ: M5
M6G-PJ: M6
M7G-PJ: M7

Maximum Ratings and Electrical Characteristics

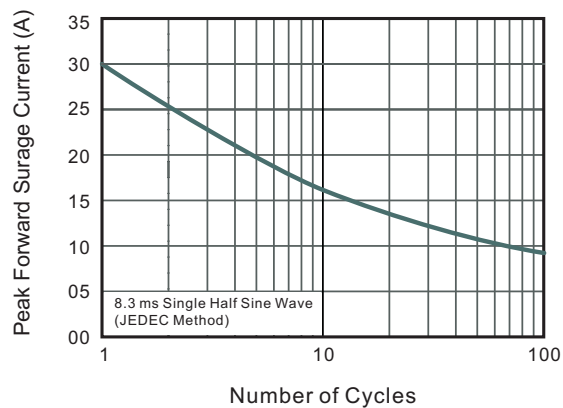
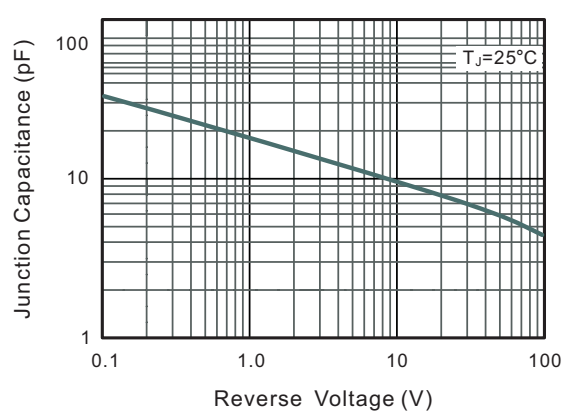
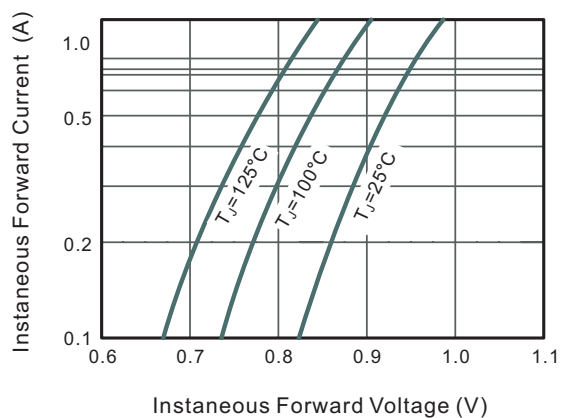
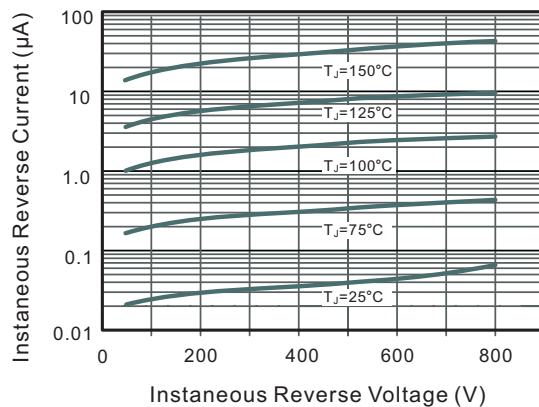
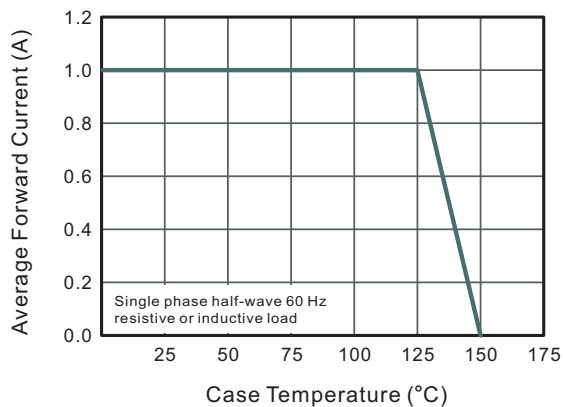
Ratings at 25°C ambient temperature unless otherwise specified. Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20 %.

Parameter	Symbols	M1G-PJ	M2G-PJ	M3G-PJ	M4G-PJ	M5G-PJ	M6G-PJ	M7G-PJ	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	1.0							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load	I_{FSM}	30							A
Maximum Instantaneous Forward Voltage at 1 A	V_F	1.1							V
Maximum DC Reverse Current at Rated DC Blocking Voltage $T_A = 25\text{ }^{\circ}\text{C}$ $T_A = 125\text{ }^{\circ}\text{C}$	I_R	5 50							μA
Typical Junction Capacitance ^{Note1}	C_j	15							pF
Typical Thermal Resistance ^{Note2}	$R_{\theta JA}$	75							$^{\circ}\text{C/W}$
Junction Temperature	T_J	150							$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150							$^{\circ}\text{C}$

Note:

1. Measured at 1 MHz and applied reverse voltage of 4 V DC.
2. P.C.B. mounted with 1.0" X 1.0" (2.54X 2.54 cm) copper pad areas.

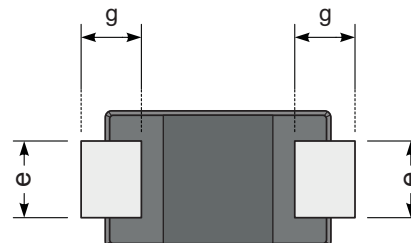
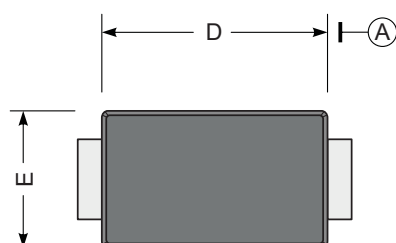
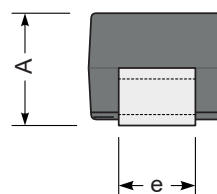
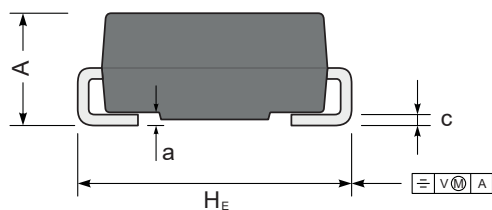
Typical Characteristic Curves



Package Outline

SMA

Dimensions in mm



UNIT		A	D	E	H _E	c	e	g	a
mm	max	2.2	4.5	2.7	5.2	0.31	1.6	1.5	0.3
	min	1.9	4.0	2.3	4.7	0.15	1.3	0.9	
mil	max	87	181	106	205	12	63	59	12
	min	75	157	91	185	6	51	35	